

## P-Channel High Density Trench MOSFET

### Features:

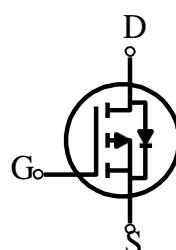
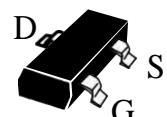
- Super high dense cell trench design for low RDS(on).
- Rugged and reliable.
- Surface Mount package.

### PRODUCT SUMMARY

VDSS	ID	RDS(on) (m-ohm) Max
-20V	-2.3	150 @ VGS= 4.5V
	-1.8	200 @ VGS= 2.5V

**MARKING : 21E**

SOT-523



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	-20	V
Gate-Source Voltage	VGS	$\pm 8$	V
Drain Current-Continuous <sup>a</sup> @ $T_A = 25^\circ\text{C}$ b -Pulse	ID	-2.3	A
	IDM	-8	A
Drain-Source Diode Forward Current <sup>a</sup>	IS	-0.75	A
Maximum Power Dissipation <sup>a</sup>	PD	0.7	W
		0.25	
Operating Junction and Storage Temperature Range	TJ,TSTG	- 55 to 150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Thermal Resistance,Junction-to-Ambient <sup>a</sup>	RthJA	125	$^\circ\text{C/W}$
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Note

a. Surface Mounted on FR4 Board ,  $t \leq 10\text{sec}$ .

b. Pulse width limited by maximum junction temperature.



**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V , I <sub>D</sub> = -250uA	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -20V , V <sub>GS</sub> = 0V			-1	uA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±8V , V <sub>DS</sub> = 0V			-100	nA
<b>ON CHARACTERISTICS</b> <sup>b</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250uA	-0.45	-0.65	-0.95	V
Drain-Source On-State Resistance	R <sub>DSS(on)</sub>	V <sub>GS</sub> = -4.5V , I <sub>D</sub> = -2.3A		125	150	m-ohm
		V <sub>GS</sub> = -2.5V , I <sub>D</sub> = -1.8A		170	200	m-ohm
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b> <sup>b</sup>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V , I <sub>S</sub> = -0.75A			-1.2	V
<b>DYNAMIC CHARACTERISTICS</b> <sup>c</sup>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = -15V , V <sub>GS</sub> = 0V f = 1.0MHz		435		pF
Output Capacitance	C <sub>OSS</sub>			121		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			78		pF
<b>SWITCHING CHARACTERISTICS</b> <sup>c</sup>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = -10V , I <sub>D</sub> = -1A V <sub>GEN</sub> = -4.5V R <sub>L</sub> = 6 ohm R <sub>GEN</sub> = 6 ohm		9.5		ns
Rise Time	t <sub>r</sub>			4.2		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			29.5		ns
Fall Time	t <sub>f</sub>			13.7		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -10V I <sub>D</sub> = -2.3A V <sub>GS</sub> = -4.5V		8.6		nC
Gate-Source Charge	Q <sub>gs</sub>			1.7		nC
Gate-Drain Charge	Q <sub>gd</sub>			1.2		nC

Note

b. Pulse Test Pulse width ≤ 300us , Duty Cycle ≤ 2% .

c. Guaranteed by design , not subject to production testing .

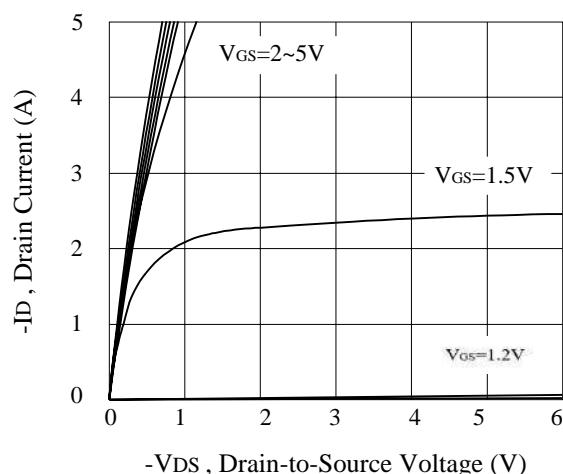


Figure 1. Output Characteristics

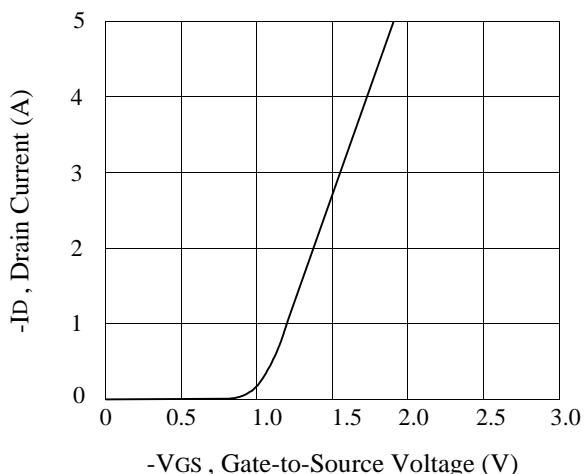


Figure 2. Transfer Characteristics

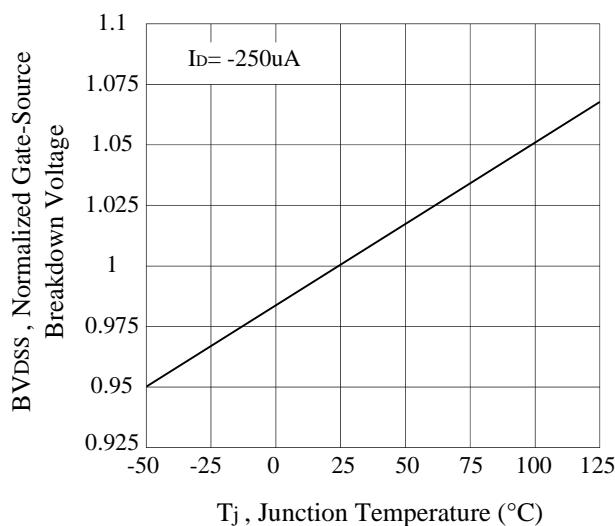


Figure 3. Breakdown Voltage Variation with Temperature

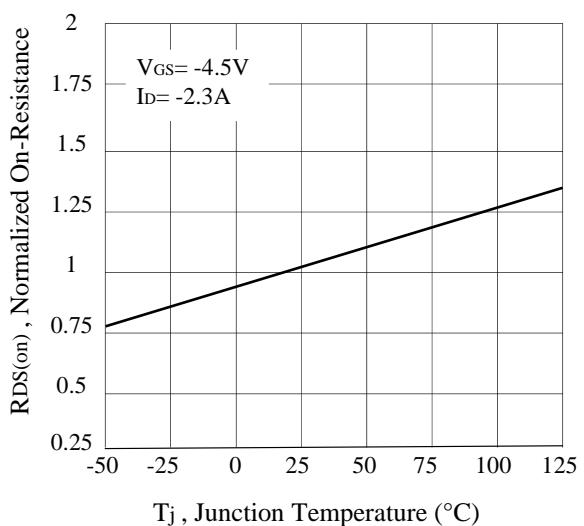


Figure 4. On-Resistance Variation with Temperature

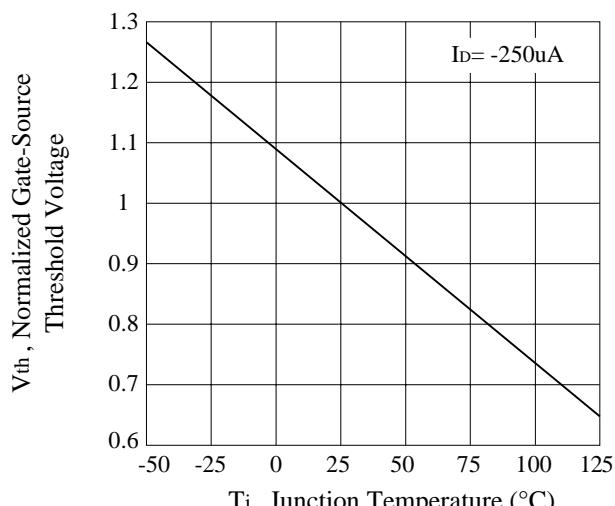


Figure 5. Gate Threshold Variation with Temperature

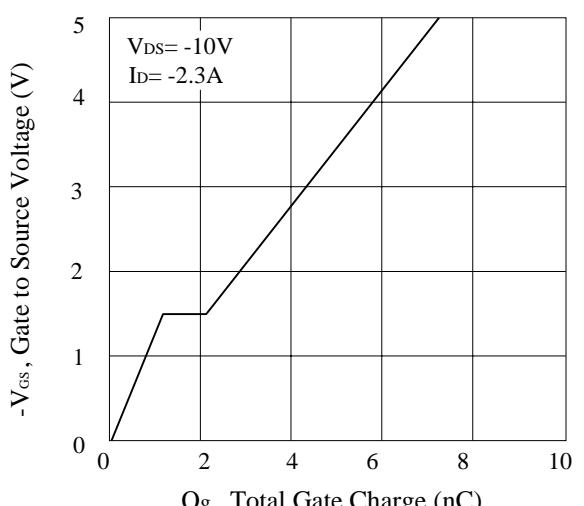
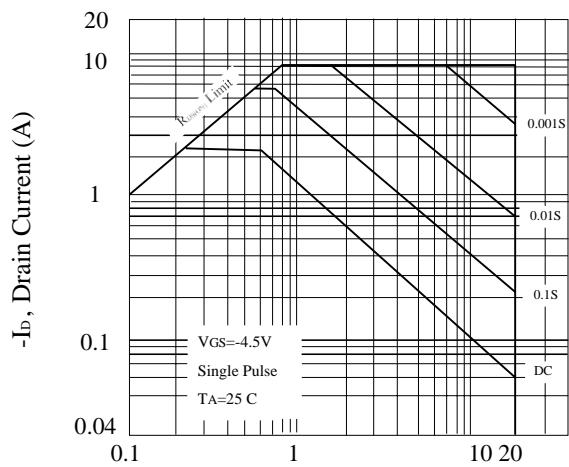
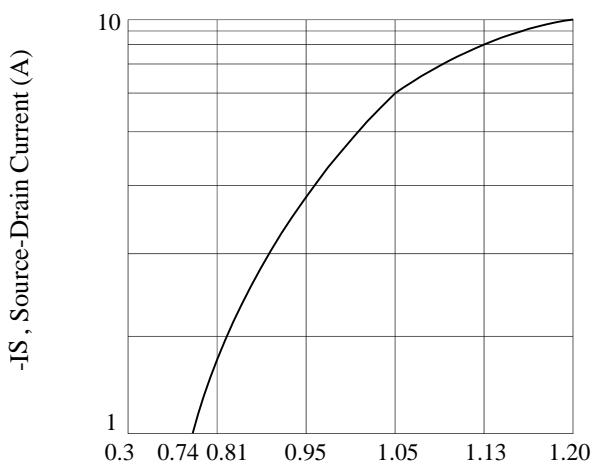


Figure 6. Gate Charge



-VDS , Drain-Source Voltage (V)  
 Figure 7. Maximum Safe Operating Area



-VSD , Body Diode Forward Voltage (V)  
 Figure 8. Body Diode Forward Voltage Variation with Source Current

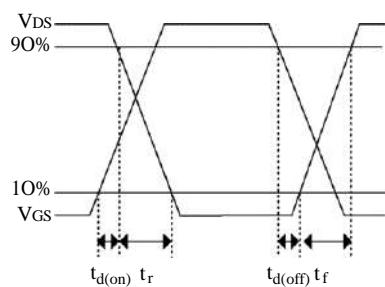
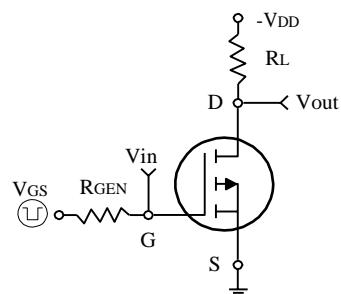


Figure 9. Switching Test Circuit and Switching Waveforms

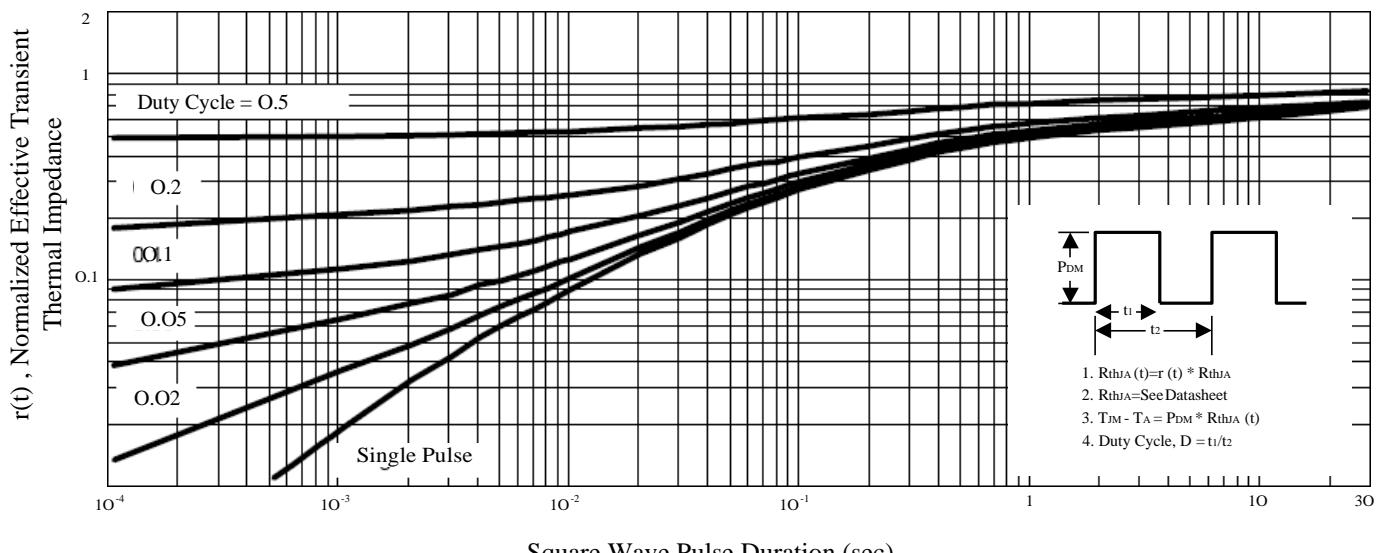
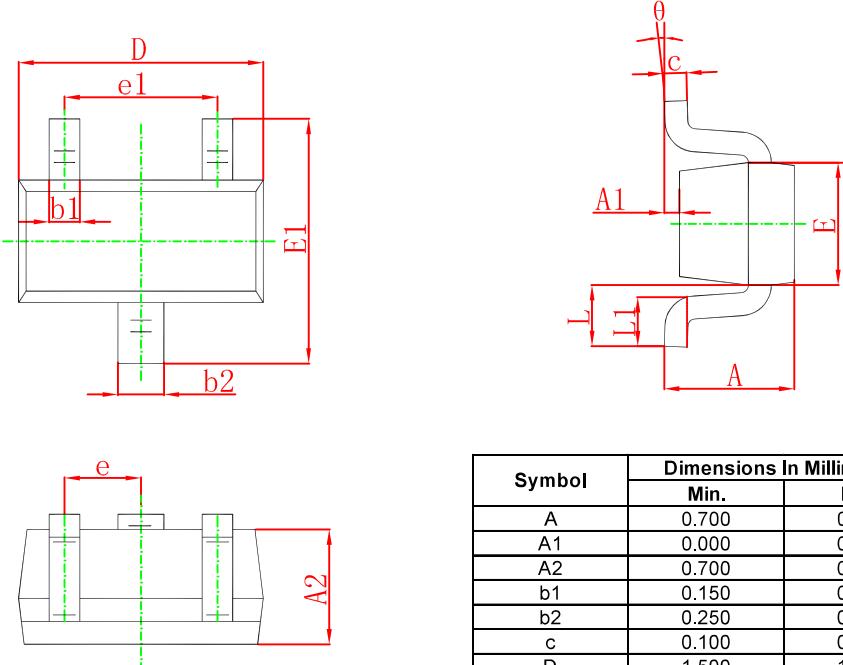


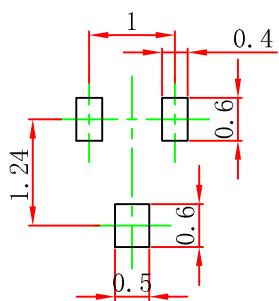
Figure 10. Normalized Thermal Transient Impedance Curve

### SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

### SOT-523 Suggested Pad Layout



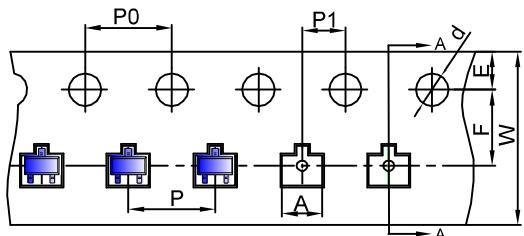
Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.

## SOT-523 Tape and Reel

### SOT-523 Tape and reel

#### SOT-523 Embossed Carrier Tape



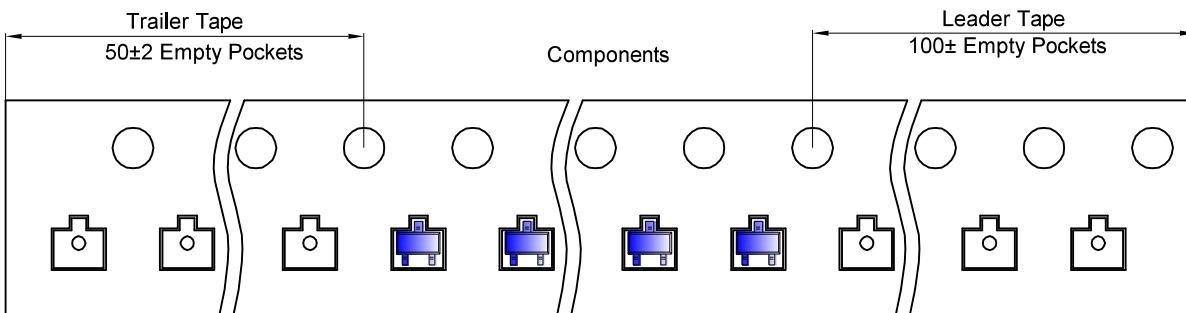
#### Packaging Description:

SOT-523 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

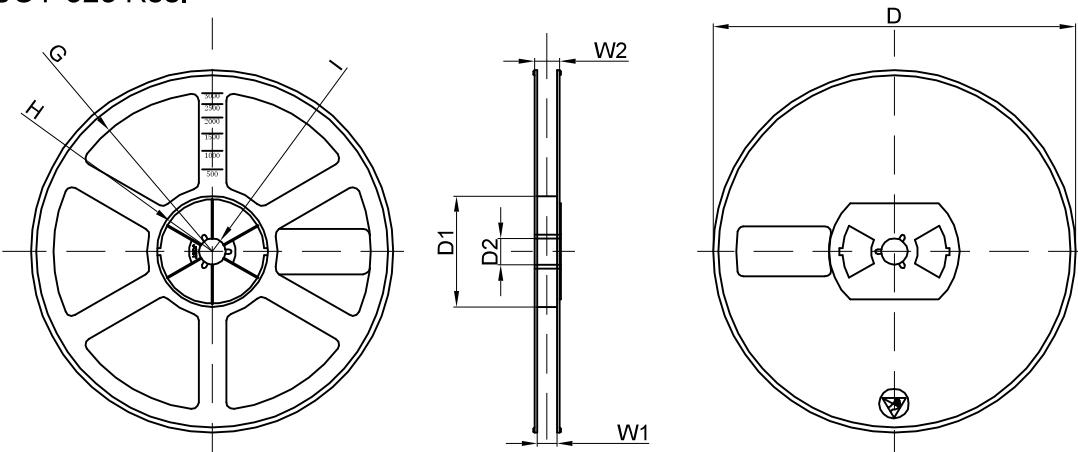
Dimensions are in millimeter

Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-523	1.85	1.85	0.875	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

#### SOT-523 Tape Leader and Trailer



#### SOT-523 Reel



Dimensions are in millimeter

Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	